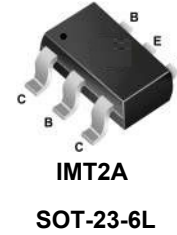
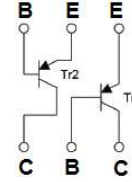


### Features

- Two 2SA1037AK chips in a package.
- Transistor Elements are Independent, Eliminating Interference.
- Mounting Cost and Area Can be cut in Half.



### Mechanical Data

- Case: SOT-23-6L
- Molding compound, UL flammability classification rating 94V-0.
- Terminals: Matte tin plated leads, solderable per MIL-STD-202, Method 208.

### Maximum Ratings (@ $T_A=25^{\circ}\text{C}$ unless otherwise specified For Tr1 and Tr2 in common)

Symbol	Parameter	Value	Units
<b>MAXIMUM RATINGS</b>			
$V_{CBO}$	Collector-Base Voltage	-60	V
$V_{CEO}$	Collector-Emitter Voltage	-50	V
$V_{EBO}$	Emitter-Base Voltage	-6	V
$I_C$	Collector Current - Continuous	-0.15	A
<b>Thermal Characteristic</b>			
$P_D$ (Note 1,2)	Power Dissipation $T_a=25^{\circ}\text{C}$	300	mW
$T_J$	Junction Temperature	-55~150	$^{\circ}\text{C}$
$T_{STG}$	Junction and Storage Temperature	-55 to +150	$^{\circ}\text{C}$

Notes:1、 Each terminal mounted on a reference land.

2、 200mW per element must not be exceeded.



# IMT2A Dual Bipolar Transistor(PNP+PNP)



## Electrical Characteristics (@ $T_A=25^\circ\text{C}$ unless otherwise specified For Tr1 and Tr2 in common)

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=-50\mu\text{A}, I_E=0$	-60	-	-	V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=-1\text{mA}, I_B=0$	-50	-	-	V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=-50\mu\text{A}, I_C=0$	-6	-	-	V
Collector cut-off current	$I_{CBO}$	$V_{CB}=-60\text{V}, I_E=0$	-	-	-100	nA
Emitter cut-off current	$I_{EBO}$	$V_{EB}=-6\text{V}, I_C=0$	-	-	-100	nA
DC Current Gain	$h_{FE}$	$V_{CE} = -6\text{V}, I_C = -1\text{mA}$	120	-	560	-
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C=-50\text{mA}, I_B=-5\text{mA}$	-	-	-0.5	V
Transition frequency	$f_T$	$V_{CE}=-12\text{V}, I_E=2\text{mA}$ $f=100\text{MHz}$	-	140	-	MHz
Collector output capacitance	$C_{obo}$	$V_{CB}=-12\text{V}, f=1\text{MHz}$	-	4	5	pF

## Ratings and Characteristic Curves ( $T_A=25^\circ\text{C}$ unless otherwise noted)

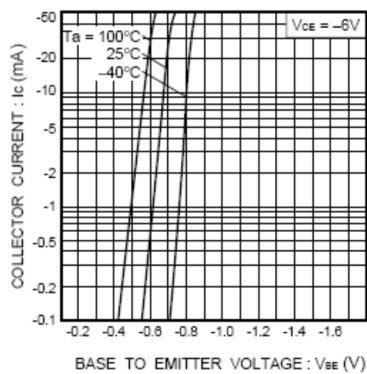


Fig.1 Grounded emitter propagation characteristics

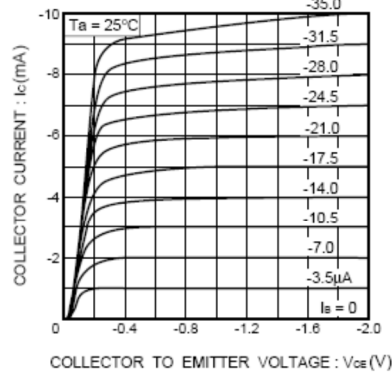


Fig.2 Grounded emitter output characteristics ( I )

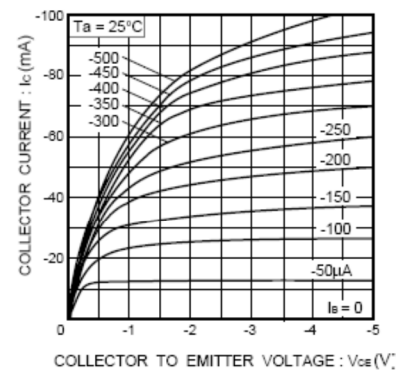


Fig.3 Grounded emitter output characteristics ( II )

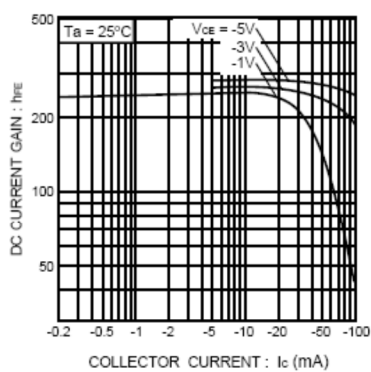


Fig.4 DC current gain vs. collector current ( I )

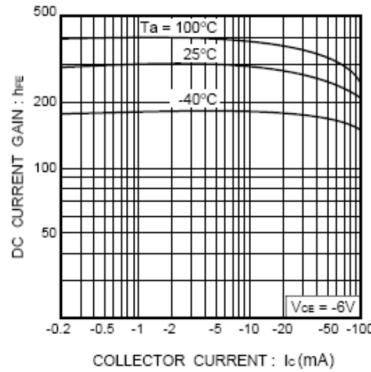


Fig.5 DC current gain vs. collector current ( II )

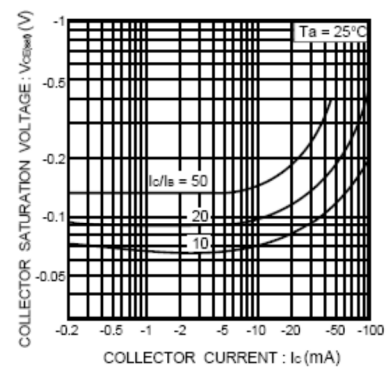


Fig.6 Collector-emitter saturation voltage vs. collector current ( I )

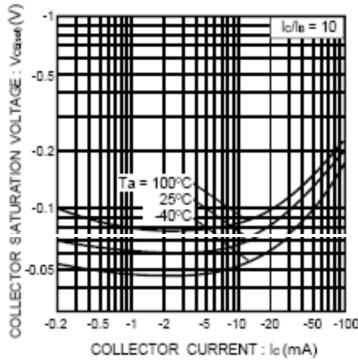


Fig.7 Collector-emitter saturation voltage vs. collector current ( II )

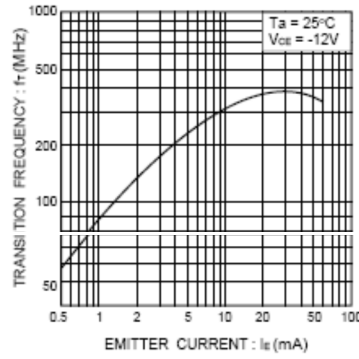


Fig.8 Gain bandwidth product vs. emitter current

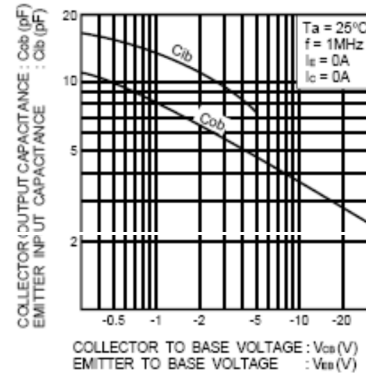
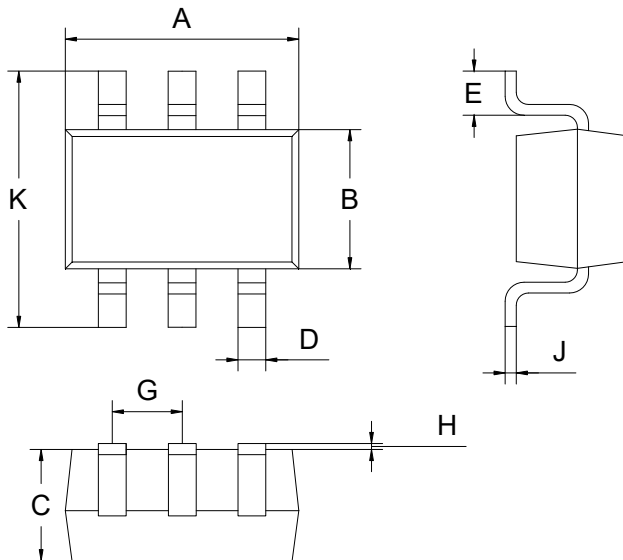


Fig.9 Collector output capacitance vs. collector-base voltage  
Emitter input capacitance vs. emitter-base voltage

### Package Outline Dimensions(unit:mm)

#### SOT-23-6L



SOT-23-6L		
Dim	Min	Max
A	2.80	3.00
B	1.50	1.70
C	1.00	1.20
D	0.35	0.45
E	0.35	0.55
G	0.90	1.00
H	0.02	0.10
J	0.10	0.20
K	2.60	3.00



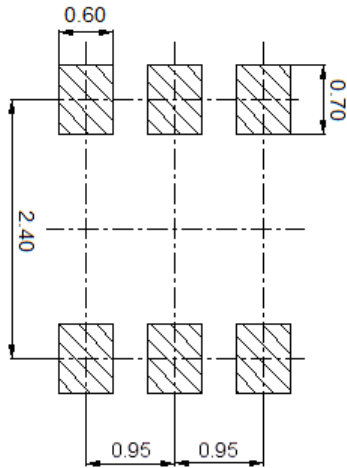
# IMT2A

Dual Bipolar Transistor(PNP+PNP)



## SOLDERING FOOTPRINT(unit:mm)

### SOT-23-6L



## Ordering Information

Part Number	Package	Shipping	Marking Code
IMT2A	SOT-23-6L	3000/Tape&Reel	T2